	120A
	40V
	5mΩ

♦Adopt advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	40	-	-
Gate Body Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100
Zero Gate Voltage Drain Current	V_{DS} = 40 V, V_{GS} = 0 V	-	-	1
Gate Threshold Voltage	V_{DS}= V_{GS}, I_D=250μA	1		2.5

Drain-Source on-Resistance V_O t

YFW120N04NF				

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